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(54) Title: ETCHING SOLUTION AND METHOD FOR SELECTIVELY REMOVING SILICON NITRIDE DURING MANUFACTURE OF A SEMICONDUCTOR DEVICE

(57) Abstract: Described herein is an etching solution and the method of using the etching solution comprising water, phosphoric acid solution (aqueous), an organosilicon compound as disclosed herein, and a hydroxyl group-containing water-miscible solvent. Such compositions are useful for the selective removal of silicon nitride over silicon oxide

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